

05/08/2019

EES311

$$I_{DS} = \begin{cases} \mu_n C_{ox} \frac{W}{L} V_{DS} [(V_{GS} - V_T) - V_{DS}/2] \\ \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)^2 \\ \sim 0 \end{cases}$$

$$V_{DS} \leq V_{GS} - V_T$$

$$V_{DS} \geq V_{GS} - V_T$$

$$V_{GS} < V_T$$

NPTEL

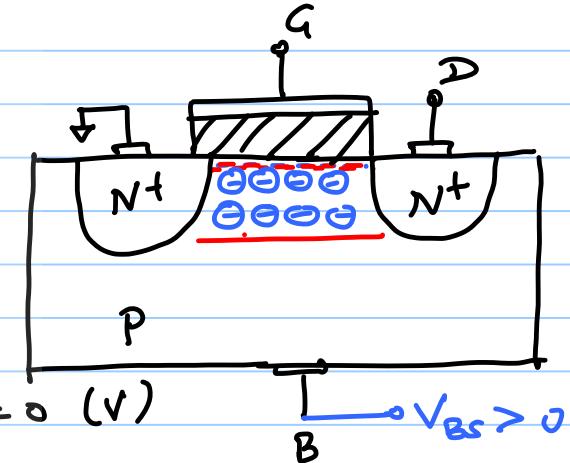
Body Effect

$$V_{TH} = \psi_s + \frac{1}{C_{ox}} \sqrt{2\epsilon_s q N_A |\psi_s|} \quad \leftarrow$$

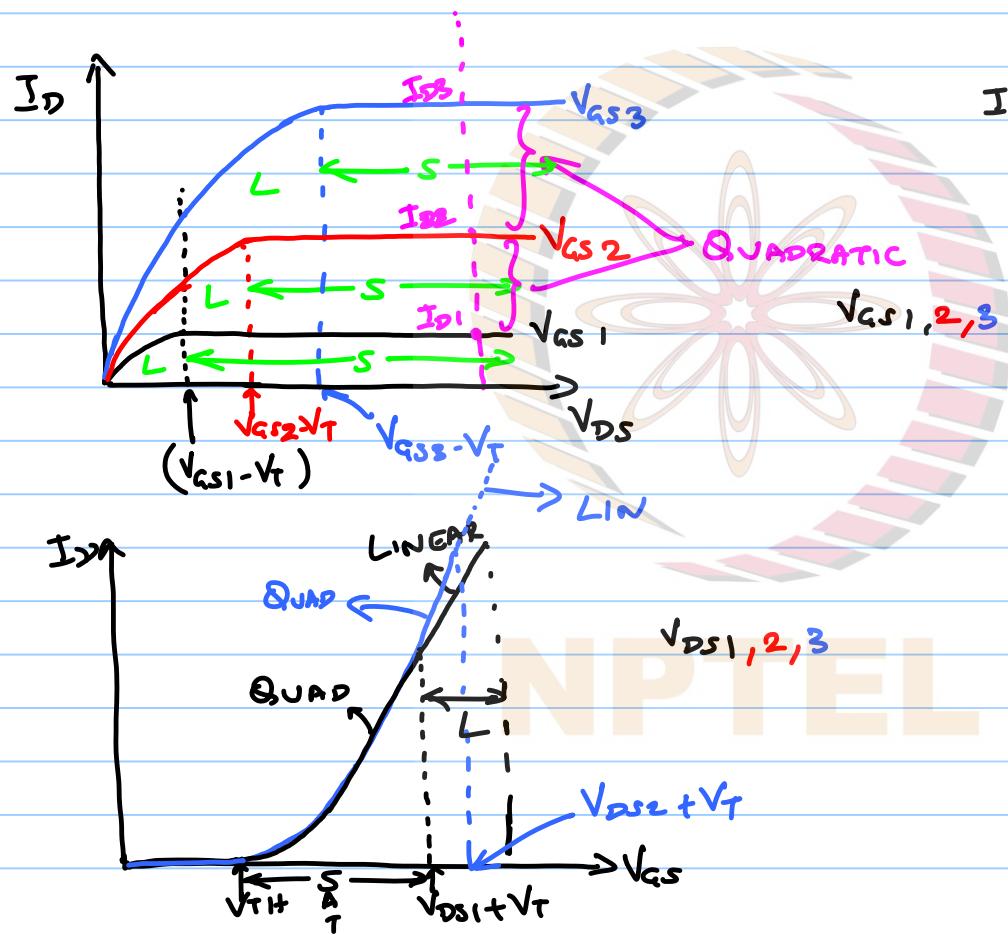
$$V_{TH} = V_{TH0} + \gamma (\sqrt{|\psi_s + V_{SB}|} - \sqrt{|\psi_s|})$$

$V_{TH0} \rightarrow$ THRESHOLD VOLTAGE @ $V_{SB} = 0$ (V)

$\gamma \rightarrow$ BODY EFFECT Coeff > 0 (for NMOS) $\Rightarrow V_{TH} \downarrow$

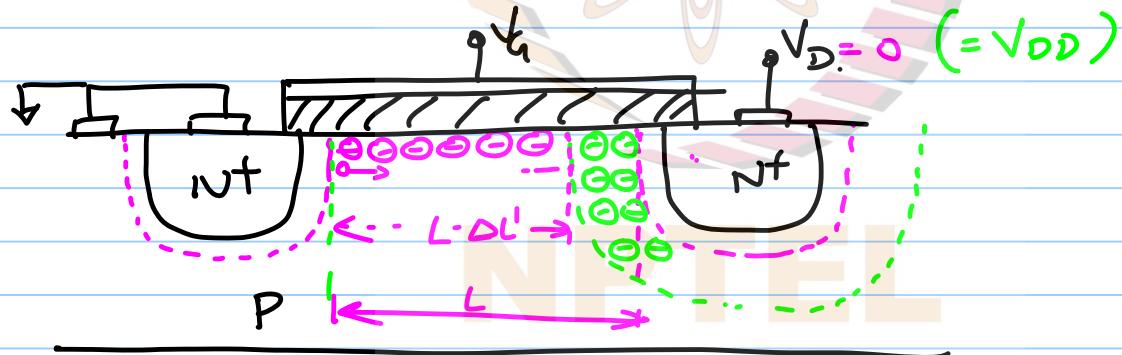
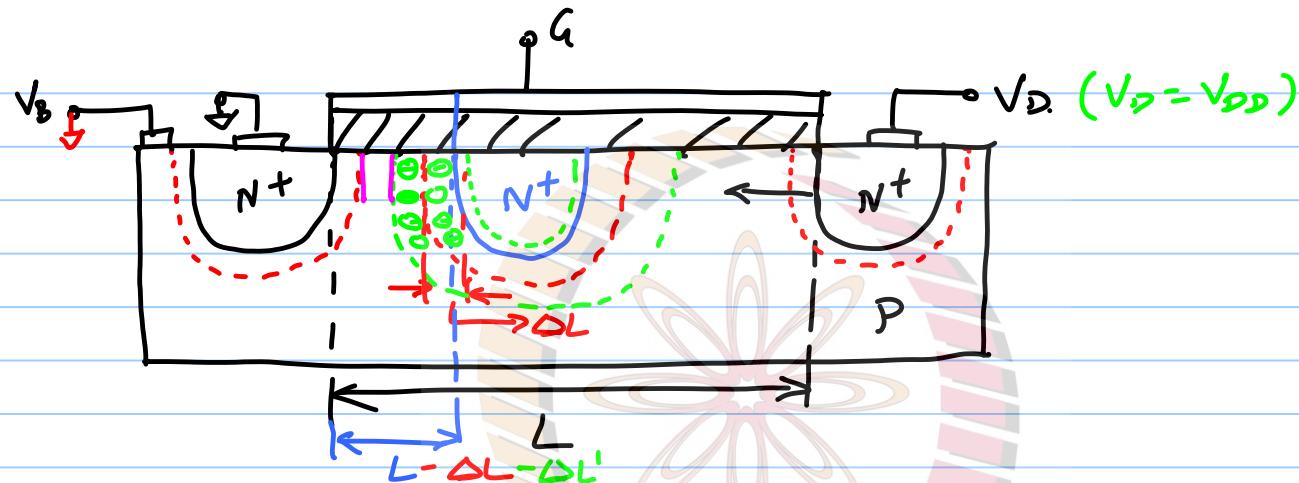


NPTEL



$$I_D = \begin{cases} \mu n C_{ox} \frac{W}{L} V_{DS} \left[\left(V_{GS} - V_T \right) - \frac{V_{DS}}{2} \right] & V_{DS} \leq V_{GS} - V_T \\ \mu n C_{ox} \frac{W}{2L} \left(V_{GS} - V_T \right)^2 & V_{DS} \geq V_{GS} - V_T \end{cases}$$

$$V_{DS} \geq V_{GS} - V_T$$



SHORT CHANNEL EFFECT:

CHANNEL LENGTH MODULATION: (CLM)

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

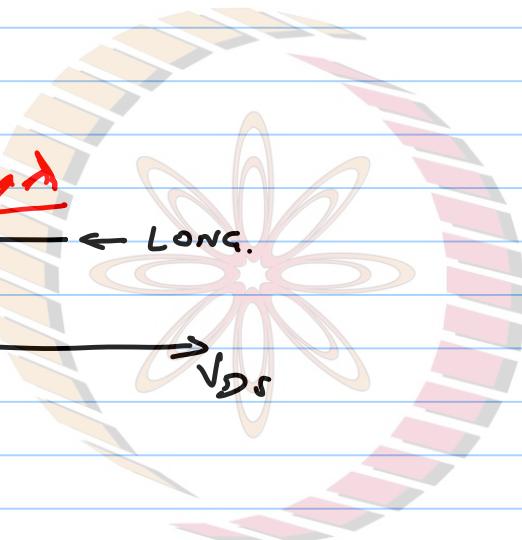
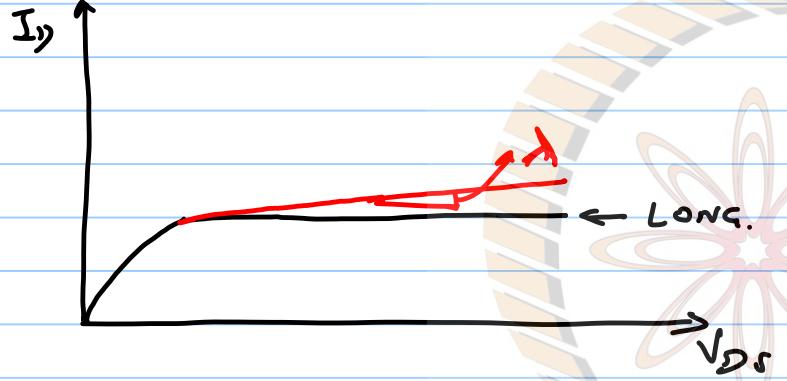
(LONG CHANNEL EQN $\neq f_n(\sqrt{ds})$)

$$L \rightarrow (L - \Delta L)$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{(L - \Delta L)} (V_{GS} - V_{TH})^2 = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2 \left(1 + \frac{\Delta L}{L}\right)$$

$$\Rightarrow I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$$

$\uparrow V_{DS}$
CLM PARAM



NPTEL